

ASC100N1700MT4L

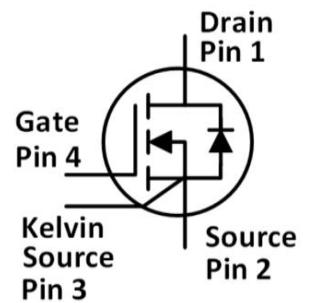
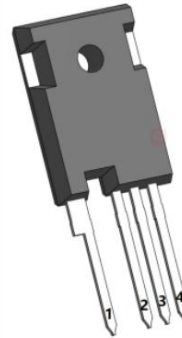
1700V N-Channel MOSFET

Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



Application

- EV motor drive
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Solar inverters
- EV charging

Ordering Information

Part Number	Marking	Package	Packaging
ASC100N1700MT4L	ASC100N1700MT4L	TO-247-4	Tube

ASC100N1700MT4L

Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1700	V
I_D	Drain Current(continuous)at $T_c=25^{\circ}\text{C}$	100	A
I_D	Drain Current(continuous)at $T_c=100^{\circ}\text{C}$	75	A
I_{DM}	Drain Current (pulsed)	200	A
V_{GS}	Gate-Source Voltage	-10/+22V	V
P_D	Power Dissipation $T_c = 25^{\circ}\text{C}$	500	W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$

Electrical Characteristics($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	1700			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1700\text{V},$ $V_{GS}=0\text{V}, T_J=25^{\circ}\text{C}$		5	100	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS}=0\text{V}; V_{GS}=-5$ to 20V		10	250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=10\text{mA}$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		18		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=18\text{V}, I_D=50\text{A}$		26	33	$\text{m}\Omega$
		$V_{GS}=18\text{V}, I_D=50\text{A}$ $T_J=175^{\circ}\text{C}$		44		$\text{m}\Omega$

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Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1200V, f=1MHz,$ $V_{AC}=25mV$		6460		pF
C_{oss}	Output Capacitance			198		pF
C_{rss}	Reverse Transfer Capacitance			16		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=50A$		52		S
E_{oss}	Coss Stored Energy	$V_{DS}=1200V, f=1MHz$		152		μJ
E_{on}	Turn-On Energy (Body Diode)	$V_{DS}=1200V,$ $V_{GS}=-5/18V, I_D=50A,$ $L=150\mu H, T_J=175^\circ C$		2.12		mJ
E_{off}	Turn-Off Energy (Body Diode)			0.75		mJ
Q_g	Total Gate Charge	$V_{DS}=1200V,$ $V_{GS}=-5V/18V, I_D=50A$		168		nC
Q_{gs}	Gate-source Charge			52		nC
Q_{gd}	Gate-Drain Charge			50		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		2.5		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=1200V,$ $V_{GS}=-5V/18V,$ $I_D=50A, L=150\mu H$ $R_{ext}=2.5\Omega$		54		ns
t_r	Rise Time			35		ns
$t_{d(off)}$	Turn-off Delay Time			65		ns
t_f	Fall Time			23		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=37.5A, T_J=25^\circ C$		3.2	6	V
		$V_{GS}=0V, I_F=37.5A, T_J=175^\circ C$		2.9	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		100		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5V, I_F=50A,$ $V_R=1200V,$ $di/dt=1900A/\mu s, T_J=175^\circ C$		102		nS
Q_{rr}	Reverse Recovery Charge			718		nC
I_{rrm}	Peak Reverse Recovery Current			20		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.30	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

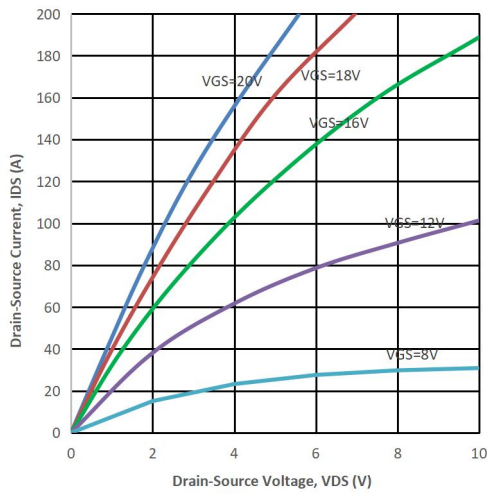


Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

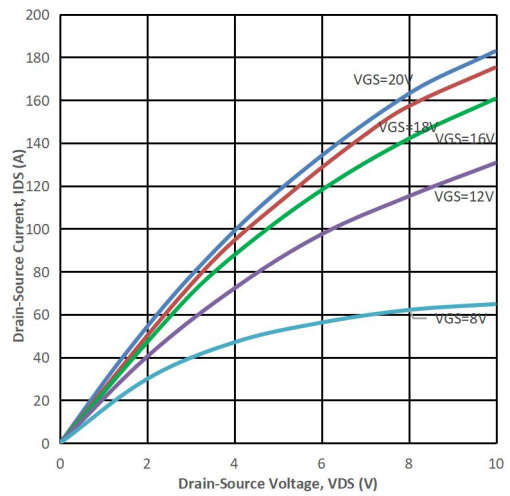


Fig3. Normalized On-Resistance vs. Temperature

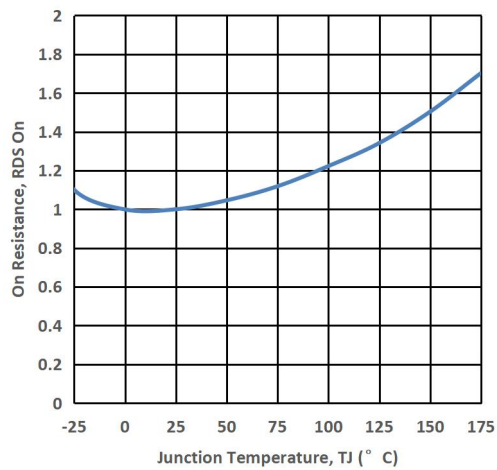


Fig4. On-Resistance vs. Temperature

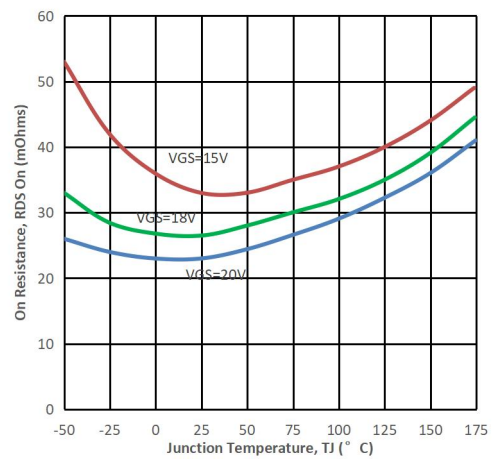


Fig5. Transfer Characteristic

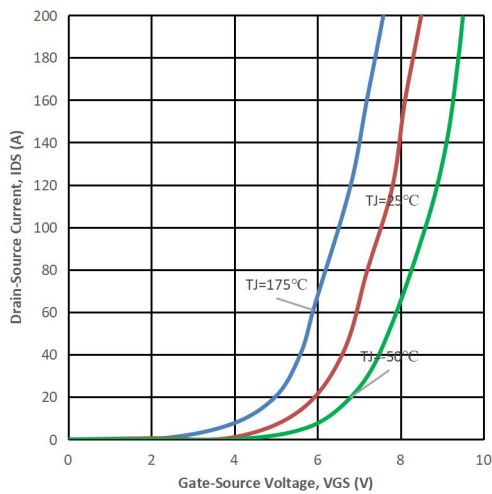


Fig6. Body Diode Characteristic at 25°C

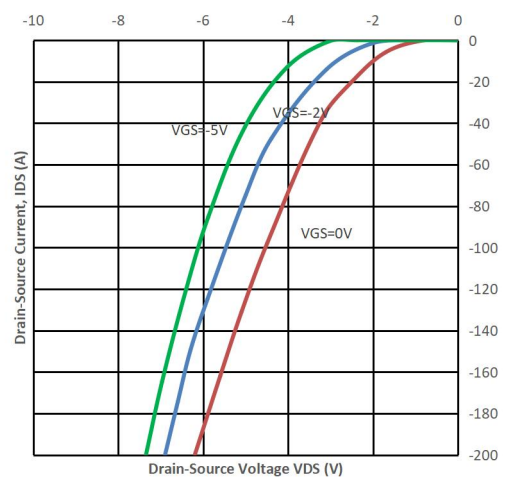


Fig7.Threshold Voltage vs. Temperature

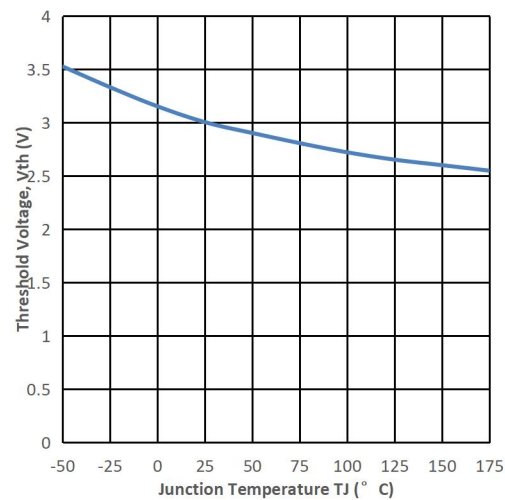


Fig8. Gate Charge Characteristics

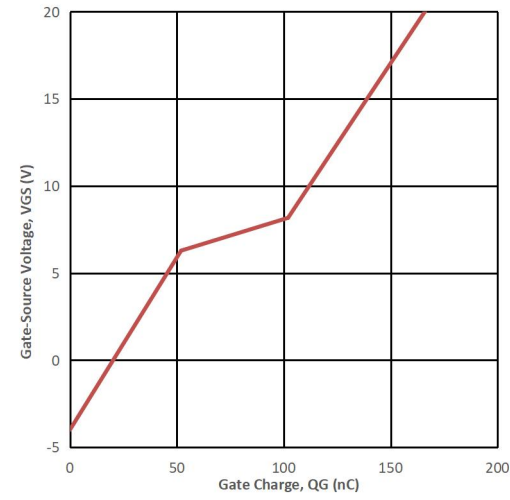


Fig9. 3rd Quadrant Characteristic at 25 $^{\circ}C$

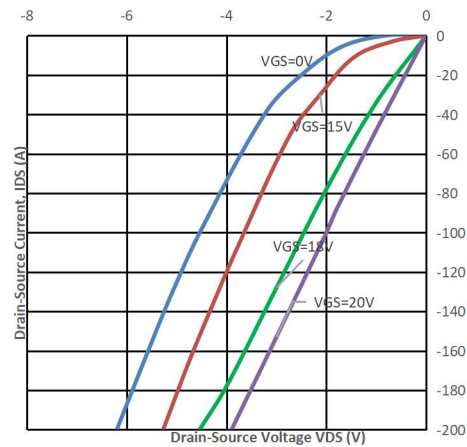


Fig10. Output Capacitor Stored Energy

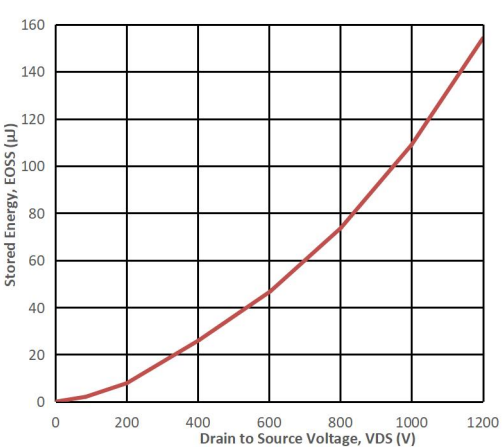


Fig11. Capacitances vs. Drain-Source

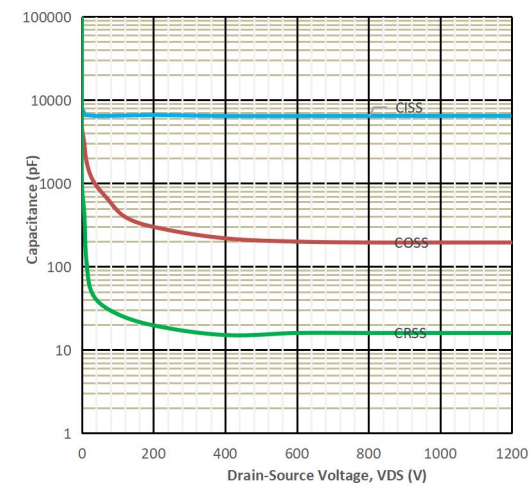


Fig12. Max Power Dissipation Derating Vs T_c

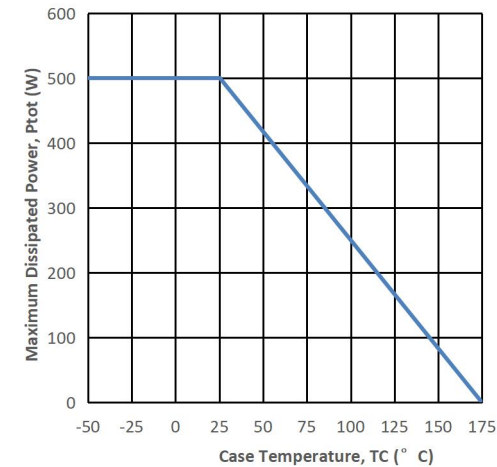


Fig13. Switching Energy vs. Drain Current

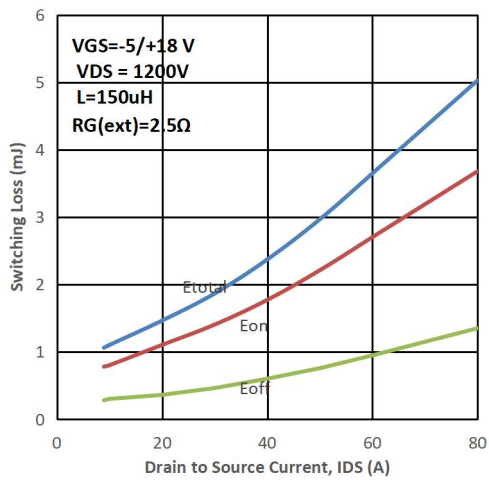


Fig14. Switching Energy vs. $R_{G(ext)}$

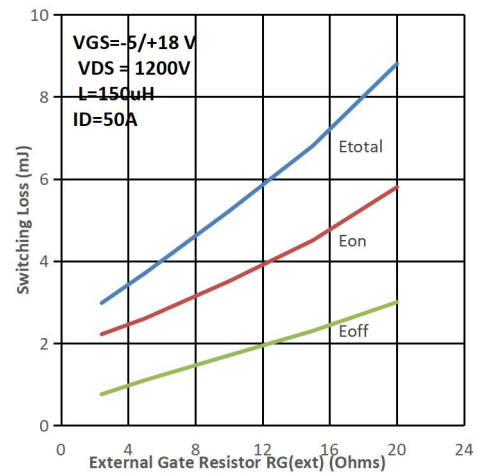


Fig15. Switching Energy vs. Temperature

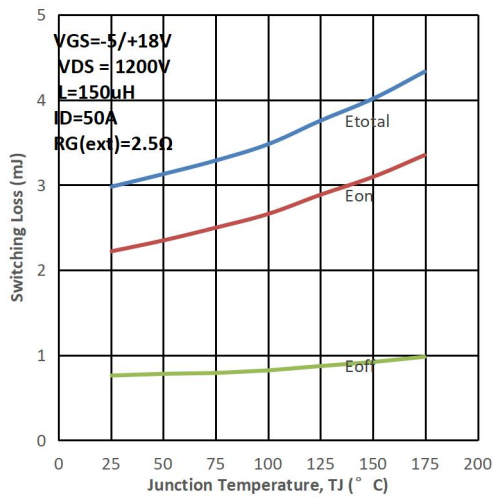


Fig16. Switching Times vs. $R_{G(ext)}$

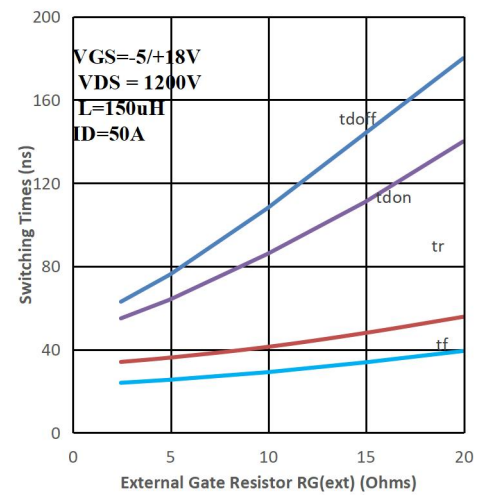


Fig17. Transient Thermal Impedance

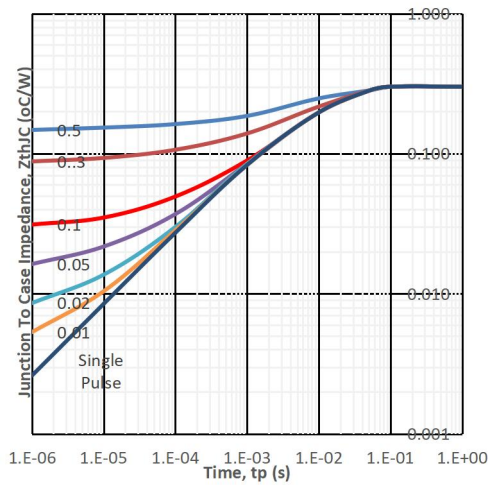
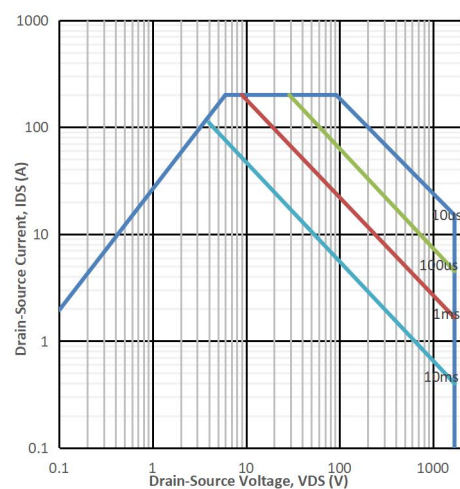


Fig18. Safe Operating Area



Notes:

- The information in this document is subject to change without notice.
- For more product and company information, please contact us or visit the website.

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